

MICRO

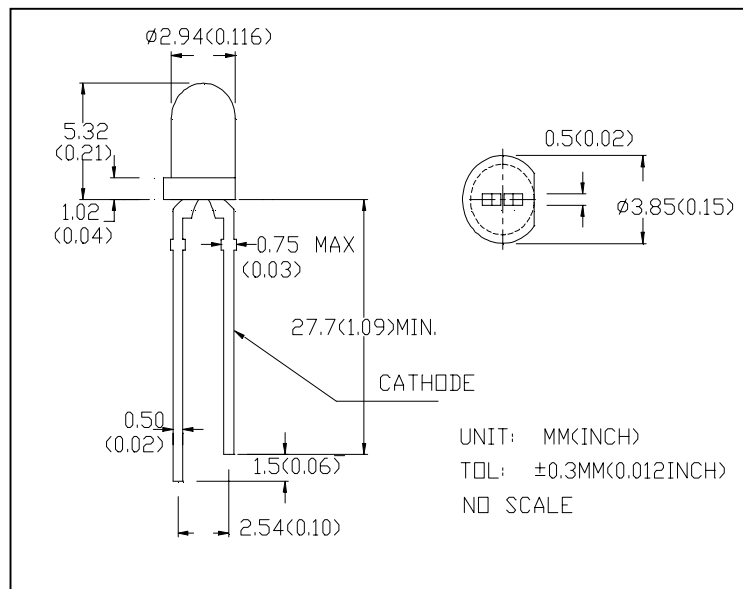
ELECTRONICS

MWB32WA-DI

**ULTRA HIGH
BRIGHTNESS
WHITE LED LAMP**

DESCRIPTION

MWB32WA-DI is an ultra high brightness InGaN/GaN white LED lamp encapsulated in a 3mm diameter white diffused lens.



ABSOLUTE MAXIMUM RATINGS

Power Dissipation @ $T_a=25^\circ\text{C}$	100mW
Forward Current, DC (IF)	30mA
Reverse Voltage	5V
Operating Temperature Range	-20 to $+80^\circ\text{C}$
Storage Temperature Range	-30 to $+100^\circ\text{C}$
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Forward Voltage	VF		3.5	4.5	V	IF=20mA
Reverse Breakdown Voltage	BVR	5			V	IR=100 μ A
Viewing Angle	2 θ 1/2		50		degree	IF=20mA
Luminous Intensity	IV	500	1500		mcd	IF=20mA
Chromaticity Coordinates	x	0.22	0.34	0.42		IF=20mA
	y	0.22	0.34	0.42		IF=20mA

CAUTION

Static electricity and surge damages the LED. It is recommended to use a wrist band or anti-electrostatic glove when handling the LED. All devices, equipment and machinery must be properly grounded.



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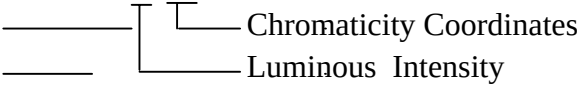
HOMEPAGE: <http://www.microelectr.com.hk>

12/5/2003

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SPECIFICATIONS FOR BIN GRADING

MWB32WA-DI-X X



PARAMETER	BIN	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS	
Luminous Intensity	1	IV	500	—	1000	mcd	IF=20mA	
	2	IV	1000	—	1500			
	3	IV	1500	—	—			
Chromaticity Coordinates	A	x	0.220	0.220	0.270	0.270	TOL: ±0.02	IF=20mA
		y	0.220	0.363	0.377	0.234		
	B	x	0.270	0.270	0.320	0.320		
		y	0.234	0.377	0.392	0.249		
	C	x	0.320	0.320	0.370	0.370		
		y	0.249	0.392	0.406	0.263		
	D	x	0.370	0.370	0.420	0.420		
		y	0.263	0.406	0.420	0.277		

CIE CHROMATICITY DIAGRAM

